

Silicon NPN Power Transistors

2SC4124

DESCRIPTION

- With TO-3PML package
- High breakdown voltage, high reliability.
- High speed
- Built in damper diode

APPLICATIONS

- Ultrahigh-definition CRT display
- Horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

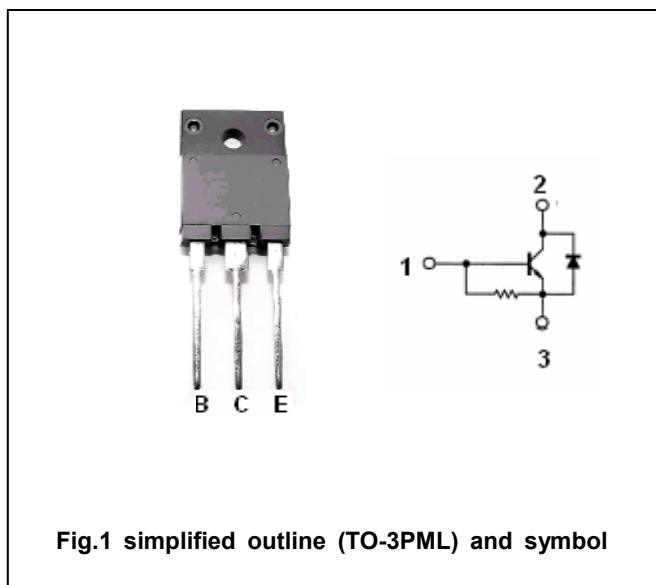


Fig.1 simplified outline (TO-3PML) and symbol

Maximum absolute ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		8	A
I _{CM}	Collector current-peak		25	A
P _C	Collector power dissipation	T _C =25°C	70	W
		T _a =25°C	3	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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PACKAGE OUTLINE

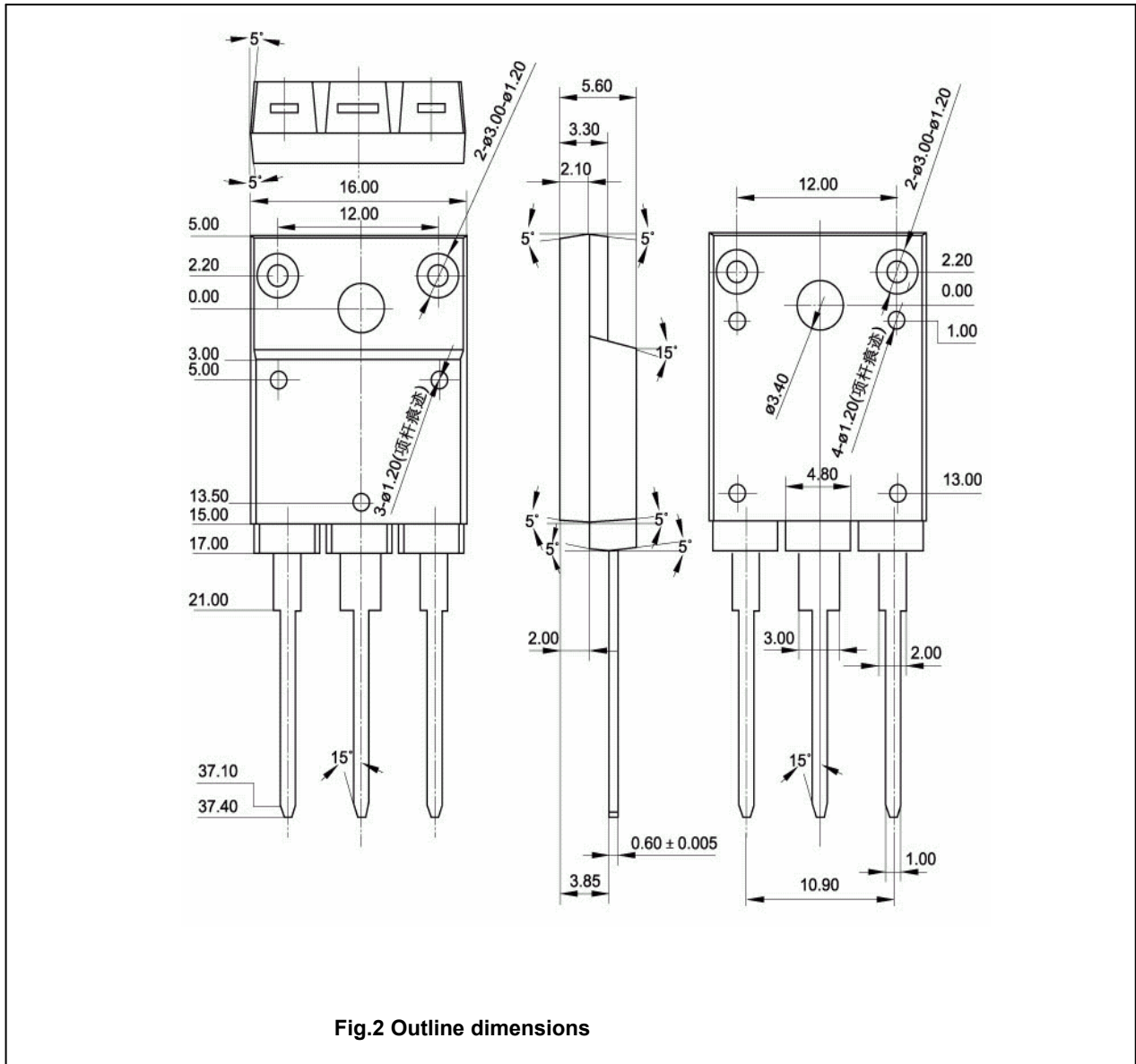


Fig.2 Outline dimensions

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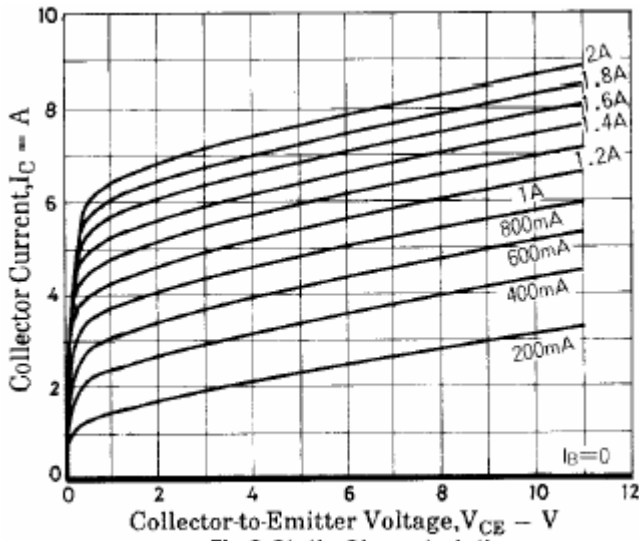


Fig.3 Static Characteristic

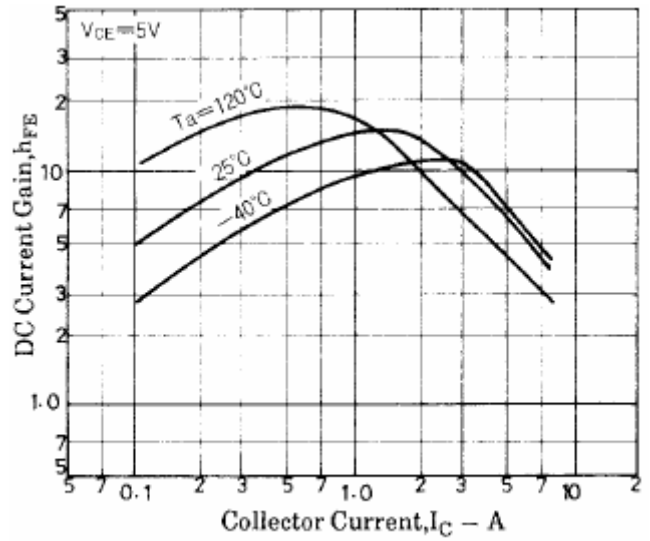


Fig.4 DC current Gain

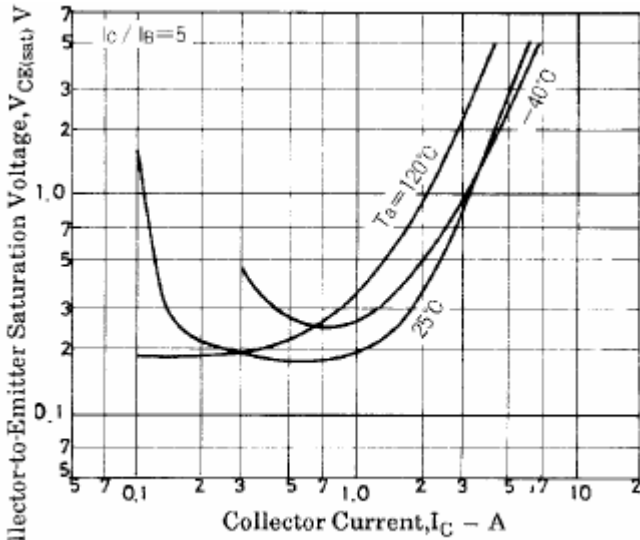


Fig.5 Collector-Emmitter Saturation Voltage

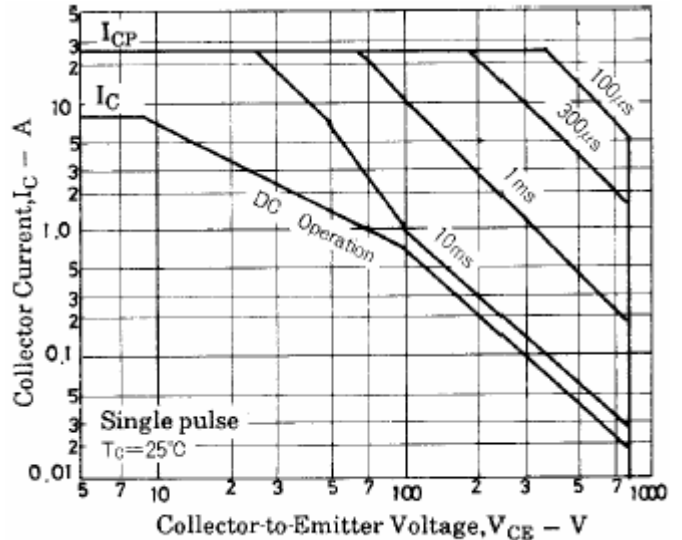


Fig.6 Safe Operating Area